

N-Channel Enhancement Mode Power MOSFET

General Description

The series of Power MOSFETs use advanced technology and design. This high voltage MOSFET fits Switched applications.

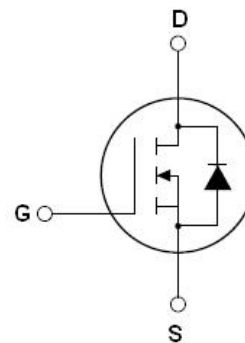
Features

- High speed switching
- Intrinsic capacitances and Qg minimized
- 100% Avalanche Tested

Application

- Switched applications

$V_{DS\ min@T_{jmax}}$	1650	V
$R_{DS(ON)TYP}$	5.5	Ω
I_D	3	A
Q_g	32	nC



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE3N150D	TO-263-2L	NCE3N150D



TO-263-2L

Table 1. Absolute Maximum Ratings ($T_J=25^\circ\text{C}$)

Parameter	Symbol	NCE3N150D	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	1500	V
Gate-Source Voltage ($V_{DS}=0V$) DC	V_{GS}	± 30	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	3	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	2.1	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	9	A
Maximum Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	187	W
Derate above 25°C		1.24	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	225	mJ
Single pulse avalanche current (Note 2)	I_{AS}	3	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	$^\circ\text{C}$

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	NCE3N150D	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.8	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	50	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=1\text{mA}$	1500			V
Zero Gate Voltage Drain Current($T_c=25^{\circ}\text{C}$)	I_{DSS}	$V_{DS}=1500\text{V}, V_{GS}=0\text{V}$			1	μA
Zero Gate Voltage Drain Current($T_c=125^{\circ}\text{C}$)	I_{DSS}	$V_{DS}=1500\text{V}, V_{GS}=0\text{V}$			100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 30\text{V}, V_{DS}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	3	4	5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=1.5\text{A}$		5.5	7.5	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=40\text{V}, V_{GS}=0\text{V},$ $F=1.0\text{MHz}$		1700		pF
Output Capacitance	C_{oss}			61		pF
Reverse Transfer Capacitance	C_{rss}			5.5		pF
Total Gate Charge	Q_g	$V_{DS}=1200\text{V}, I_D=1.5\text{A},$ $V_{GS}=10\text{V}$		32		nC
Gate-Source Charge	Q_{gs}			8.7		nC
Gate-Drain Charge	Q_{gd}			12		nC
Intrinsic gate resistance	R_G	$f = 1\text{MHz open drain}$		2		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=750\text{V}, I_D=1.5\text{A},$ $R_G=3\Omega, V_{GS}=10\text{V}$		22		nS
Turn-on Rise Time	t_r			45		nS
Turn-Off Delay Time	$t_{d(off)}$			42		nS
Turn-Off Fall Time	t_f			58		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	$T_C=25^{\circ}\text{C}$			3	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				9	A
Forward On Voltage	V_{SD}	$T_J=25^{\circ}\text{C}, I_{SD}=3\text{A}, V_{GS}=0\text{V}$		0.8	1.1	V
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}\text{C}, I_F=3\text{A},$ $di/dt=100\text{A}/\mu\text{s}$		390		nS
Reverse Recovery Charge	Q_{rr}			2.2		μC
Peak Reverse Recovery Current	I_{rrm}			11		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^{\circ}\text{C}, V_{DD}=50\text{V}, V_G=10\text{V}, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

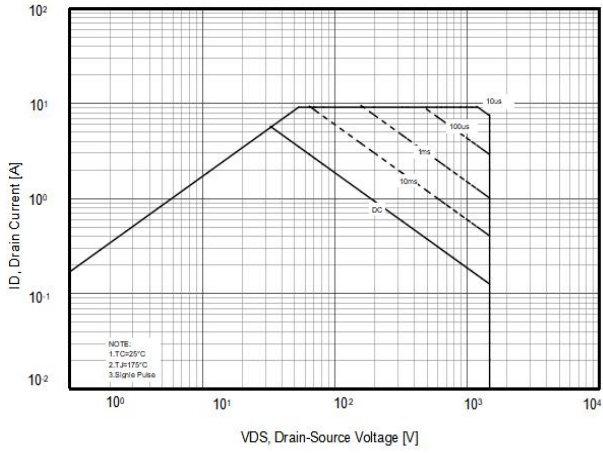


Figure2. Source-Drain Diode Forward Voltage

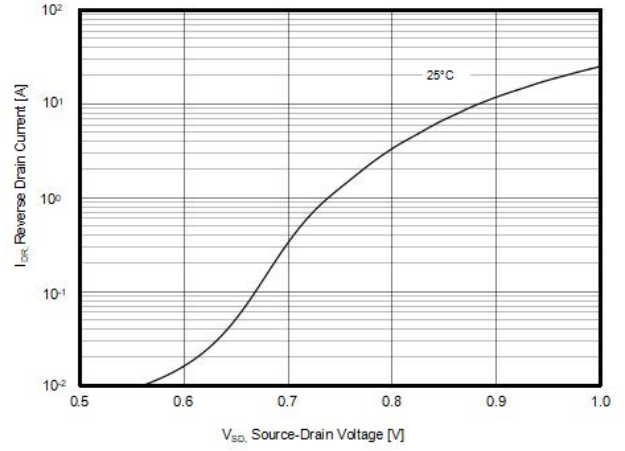


Figure3. R_{DS(ON)} vs Junction Temperature

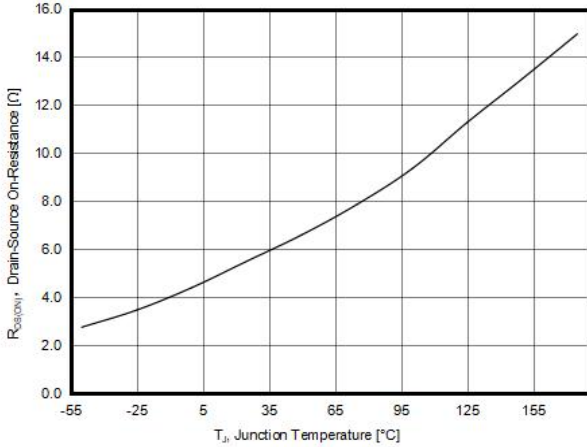


Figure4. BV_{DSS} vs Junction Temperature

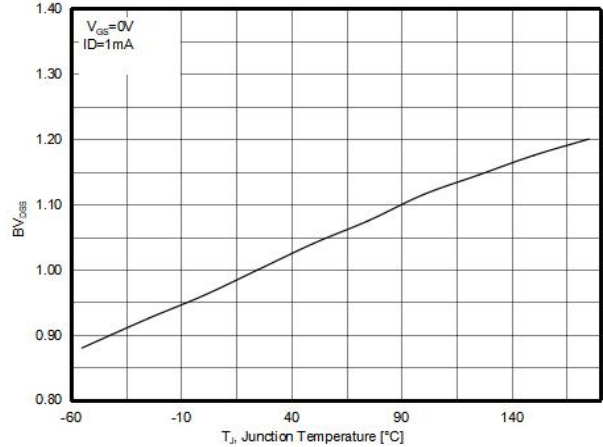


Figure5. Maximum I_D vs Junction Temperature

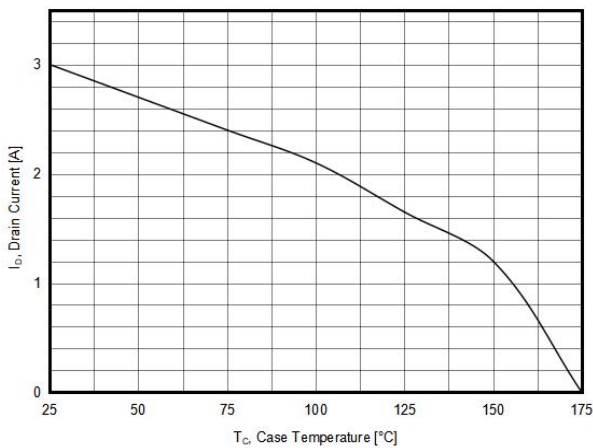


Figure6. Output characteristics

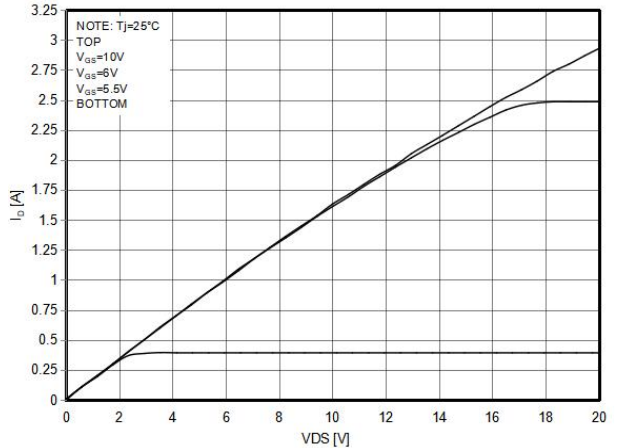


Figure7. Capacitance

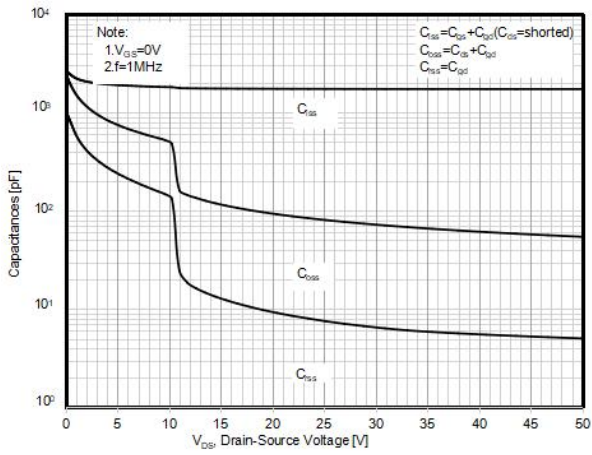


Figure8. Transfer characteristics

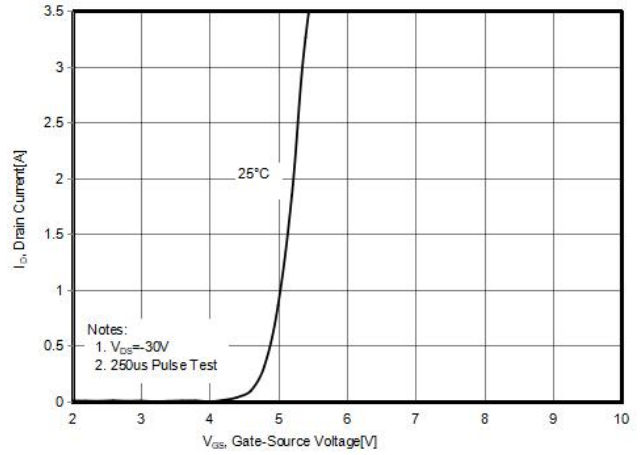


Figure9. Static drain-source on resistance

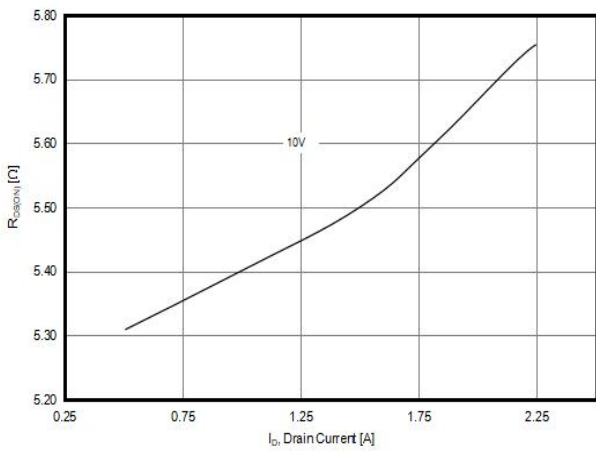
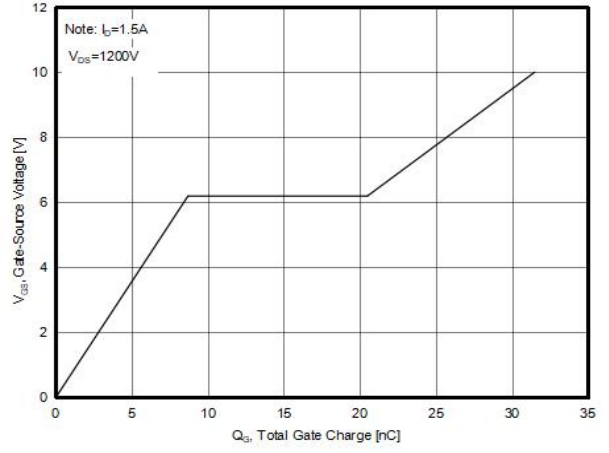


Figure9. Gate charge waveforms

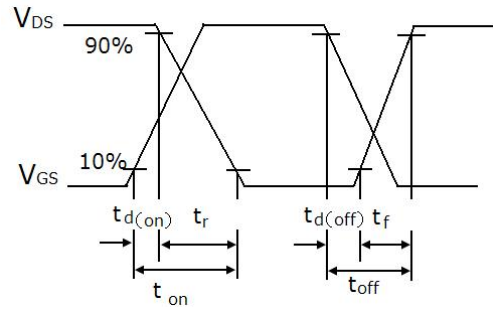


Test circuit

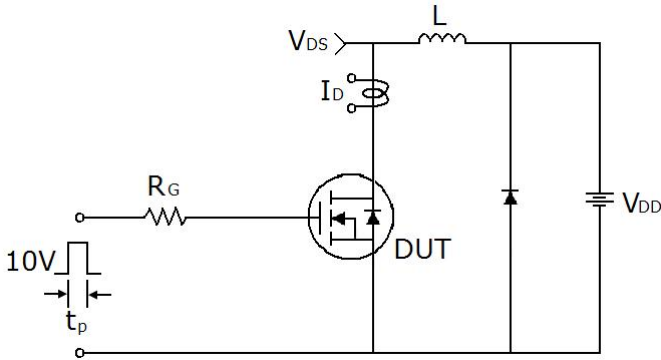
1) Gate charge test circuit & Waveform



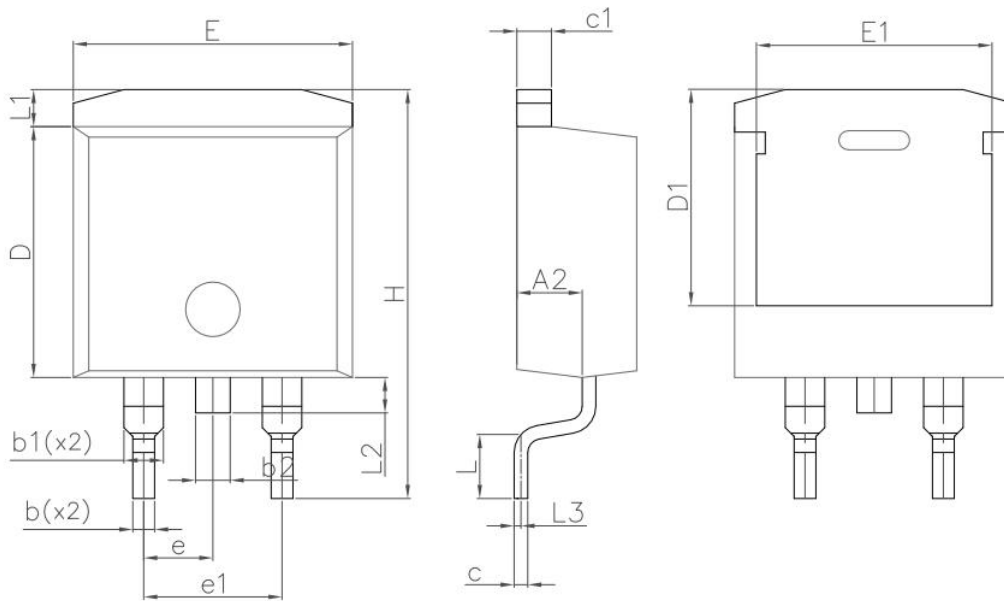
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

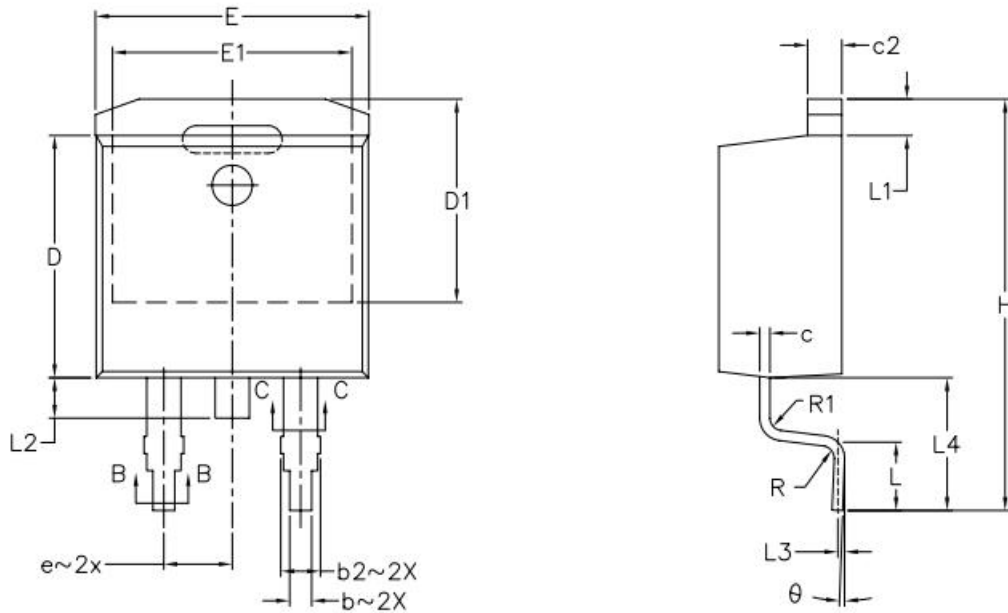


TO-263-2L-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A2	4.20	4.60	0.165	0.181
b	0.70	0.90	0.028	0.035
b1	1.20	1.75	0.047	0.069
b2	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
c1	1.15	1.40	0.045	0.055
D	9.10	9.30	0.358	0.366
D1	7.63	8.23	0.300	0.324
E	10.05	10.45	0.396	0.411
E1	8.35	8.95	0.329	0.352
e	2.54BSC		0.100BSC	
e1	5.08BSC		0.200BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.36REF		0.054REF	
L2	1.30REF		0.051REF	

TO-263-2L-J Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380
D1	6.86		0.270	
E	9.65	10.00	0.380	0.394
E1	6.22		0.245	
e	2.54BSC		0.100BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1		1.68		0.066
L2		1.78		0.070
L3	0.25BSC		0.101BSC	
L4	4.78	5.28	0.188	0.208

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